

# FGW40N65WD

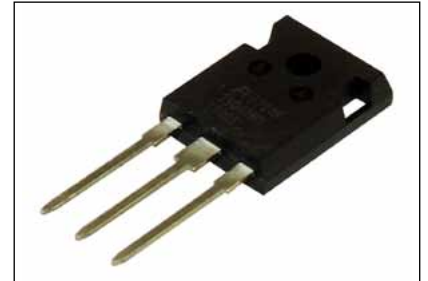
## Discrete IGBT (High-Speed W series) 650V / 40A

### Features

- Low power loss
- Low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)

### Applications

- Uninterruptible power supply
- PV Power conditioner
- Inverter welding machine



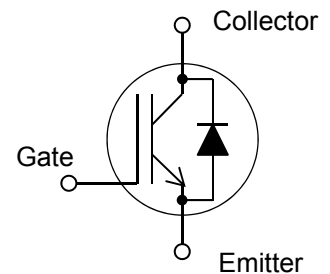
### Maximum Ratings and Characteristics

#### Absolute Maximum Ratings (at T<sub>c</sub>=25°C unless otherwise specified)

Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter Voltage	V <sub>CES</sub>	650	V	
Gate-Emitter Voltage	V <sub>GES</sub>	±20	V	
Transient Gate-Emitter Voltage		±30	V	T <sub>r</sub> <1μs
DC Collector Current	I <sub>C@25</sub>	56	A	T <sub>c</sub> =25°C
	I <sub>C@100</sub>	40	A	T <sub>c</sub> =100°C
Pulsed Collector Current	I <sub>CP</sub>	160	A	Note *1
Turn-Off Safe Operating Area		160	A	V <sub>CE</sub> ≤650V
				T <sub>j</sub> ≤175°C
Diode Forward Current	I <sub>F@25</sub>	31	A	
	I <sub>F@100</sub>	20	A	
Diode Pulsed Current	I <sub>FP</sub>	160	A	Note *1
IGBT Max. Power Dissipation	P <sub>D,IGBT</sub>	155	W	T <sub>c</sub> =25°C
FWD Max. Power Dissipation	P <sub>D,FWD</sub>	75	W	T <sub>c</sub> =25°C
Operating Junction Temperature	T <sub>j</sub>	-40 ~ +175	°C	
Storage Temperature	T <sub>stg</sub>	-55 ~ +175	°C	

Note \*1 : Pulse width limited by T<sub>jmax</sub>.

### Equivalent circuit



#### Electrical characteristics (at T<sub>j</sub>= 25°C unless otherwise specified)

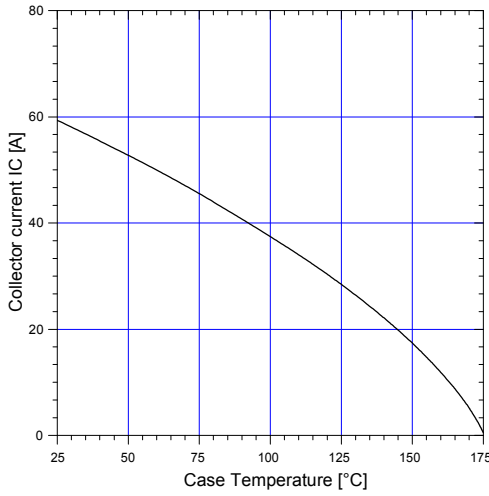
Description	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero Gate Voltage Collector Current	I <sub>CES</sub>	V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V					
		T <sub>j</sub> =25°C	-	-	250	μA	
		T <sub>j</sub> =175°C	-	-	2	mA	
Gate-Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> = 0V, V <sub>GE</sub> = ±20V	-	-	200	nA	
Gate-Emitter Threshold Voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> = 20V, I <sub>C</sub> = 40mA	3.0	4.0	5.0	V	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	V <sub>GE</sub> = 15V, I <sub>C</sub> = 40A	T <sub>j</sub> =25°C	1.40	1.80	2.20	V
			T <sub>j</sub> =125°C	-	2.05	-	
			T <sub>j</sub> =175°C	-	2.10	-	
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> =25V	1500	3000	4500	pF	
Output Capacitance	C <sub>oes</sub>	V <sub>GE</sub> =0V	43	85	128		
Reverse Transfer Capacitance	C <sub>res</sub>	f=1MHz	32	64	96		
Gate Charge	Q <sub>G</sub>	V <sub>CC</sub> = 520V I <sub>C</sub> = 40A V <sub>GE</sub> = 15V	90	180	270	nC	
Turn-On Delay Time	t <sub>d(on)</sub>	T <sub>j</sub> = 25°C, V <sub>CC</sub> = 400V I <sub>C</sub> = 20A, V <sub>GE</sub> = 15V R <sub>G</sub> = 10Ω, L = 500μH Energy loss include "tail" and FWD reverse recovery.	12	24	36	ns	
Rise Time	t <sub>r</sub>		13	25	38		
Turn-Off Delay Time	t <sub>d(off)</sub>		93	185	278		
Fall Time	t <sub>f</sub>		24	47	71		
Turn-On Energy	E <sub>on</sub>		0.15	0.29	0.44		mJ
Turn-Off Energy	E <sub>off</sub>	0.15	0.29	0.44			
Turn-On Delay Time	t <sub>d(on)</sub>	T <sub>j</sub> = 150°C, V <sub>CC</sub> = 400V I <sub>C</sub> = 20A, V <sub>GE</sub> = 15V R <sub>G</sub> = 10Ω, L = 500μH Energy loss include "tail" and FWD reverse recovery.	12	24	36	ns	
Rise Time	t <sub>r</sub>		13	25	38		
Turn-Off Delay Time	t <sub>d(off)</sub>		108	215	323		
Fall Time	t <sub>f</sub>		20	40	60		
Turn-On Energy	E <sub>on</sub>		0.25	0.50	0.75		mJ
Turn-Off Energy	E <sub>off</sub>	0.16	0.32	0.48			
Forward Voltage Drop	V <sub>F</sub>	I <sub>F</sub> =20A	T <sub>j</sub> =25°C	1.8	2.5	3.2	V
			T <sub>j</sub> =125°C	-	1.9	-	V
			T <sub>j</sub> =175°C	-	1.7	-	V
Diode Reverse Recovery Time	t <sub>rr</sub>	V <sub>CC</sub> =400V, I <sub>F</sub> =20A	31	62	93	ns	
Diode Reverse Recovery Charge	Q <sub>rr</sub>	-di <sub>F</sub> /dt=500A/μs, T <sub>j</sub> =25°C	0.13	0.26	0.39	μC	
Diode Reverse Recovery Time	t <sub>rr</sub>	V <sub>CC</sub> =400V, I <sub>F</sub> =20A	43	85	128	ns	
Diode Reverse Recovery Charge	Q <sub>rr</sub>	-di <sub>F</sub> /dt=500A/μs, T <sub>j</sub> =150°C	0.36	0.72	1.08	μC	

## ● Thermal resistance characteristics

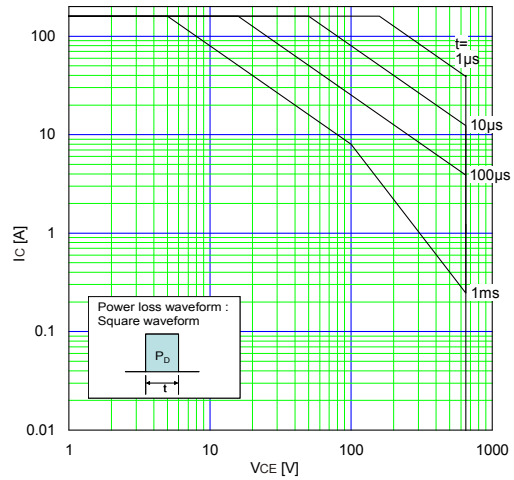
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal Resistance, Junction-Ambient	$R_{th(j-a)}$	-	-	-	50	°C/W
Thermal Resistance, IGBT Junction to Case	$R_{th(j-c)}_{IGBT}$	-	-	-	0.962	
Thermal Resistance, FWD Junction to Case	$R_{th(j-c)}_{FWD}$	-	-	-	1.923	

**Characteristics (Representative)**

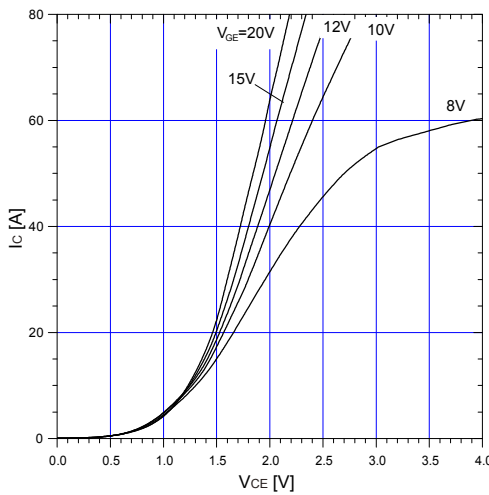
Graph.1  
DC Collector Current vs Tc  
V<sub>GE</sub> ≥ +15V, T<sub>j</sub> ≤ 175°C



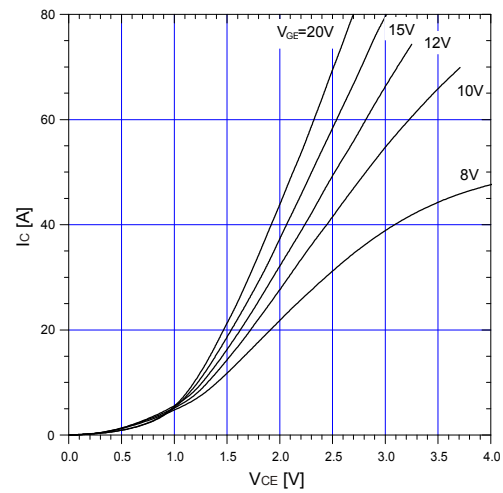
Graph.2  
SOA  
Duty=0(Single pulse), Tc=25°C



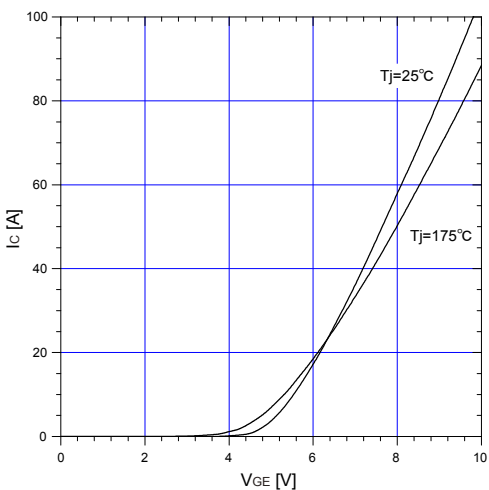
Graph.3  
Typical Output Characteristics (V<sub>CE</sub>-I<sub>C</sub>)  
T<sub>j</sub>=25°C



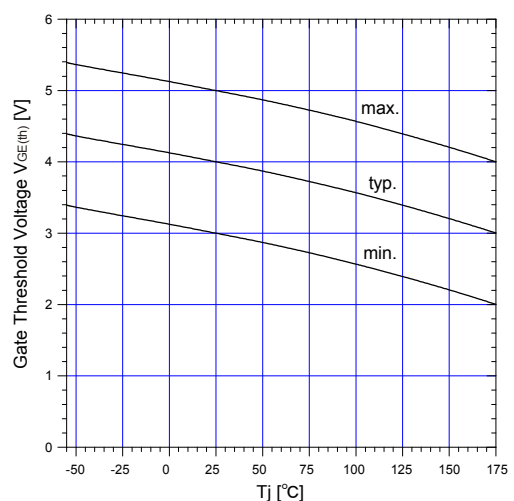
Graph.4  
Typical Output Characteristics (V<sub>CE</sub>-I<sub>C</sub>)  
T<sub>j</sub>=175°C



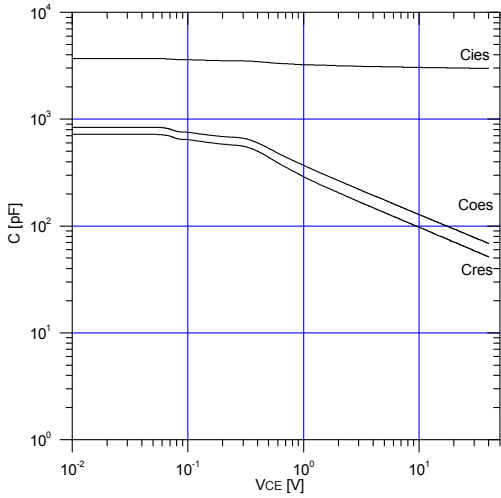
Graph.5  
Typical Transfer Characteristics  
V<sub>CE</sub>=10V



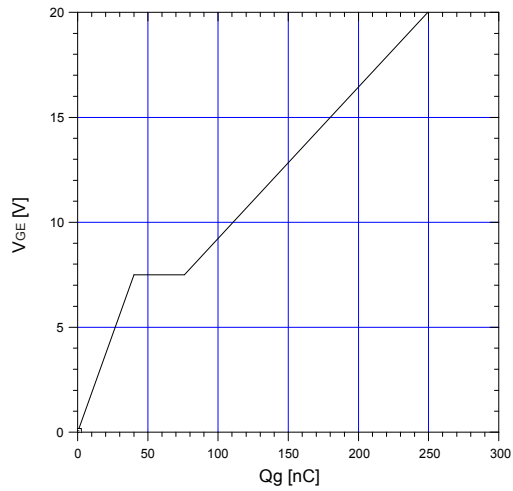
Graph.6  
Gate Threshold Voltage vs. T<sub>j</sub>  
I<sub>C</sub>=40mA, V<sub>CE</sub>=20V



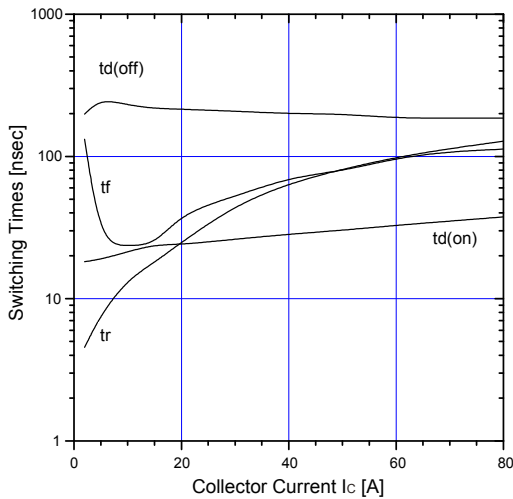
Graph.7  
Typical Capacitance  
 $V_{GE}=0V, f=1MHz, T_j=25^{\circ}C$



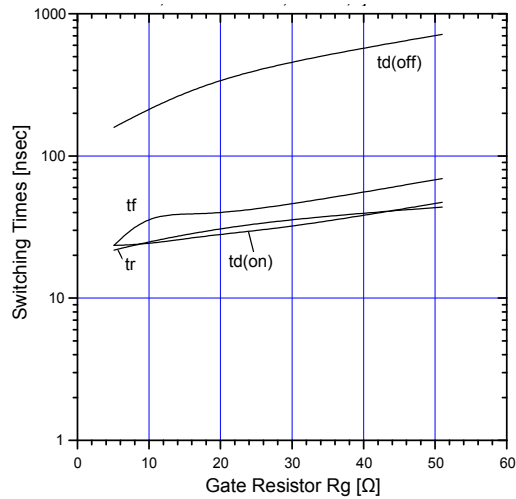
Graph.8  
Typical Gate Charge  
 $V_{cc}=520V, I_c=40A, T_j=25^{\circ}C$



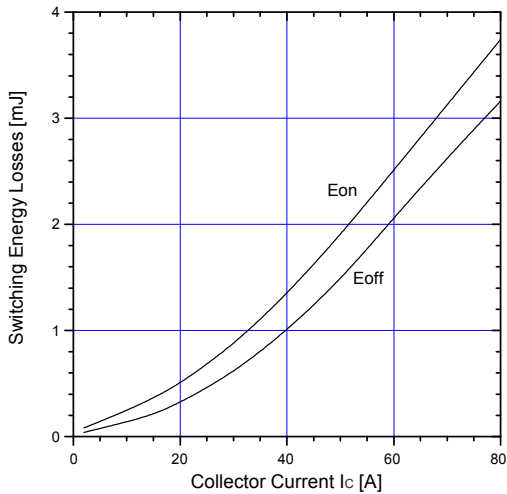
Graph.9  
Typical switching time vs. Ic  
 $T_j=150^{\circ}C, V_{cc}=400V, L=500\mu H$   
 $V_{GE}=15V, R_G=10\Omega$



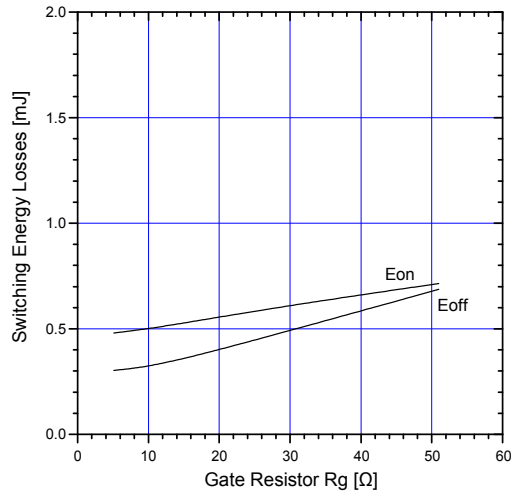
Graph.10  
Typical switching time vs. Rg  
 $T_j=150^{\circ}C, V_{cc}=400V, I_c=20A, L=500\mu H$   
 $V_{GE}=15V$



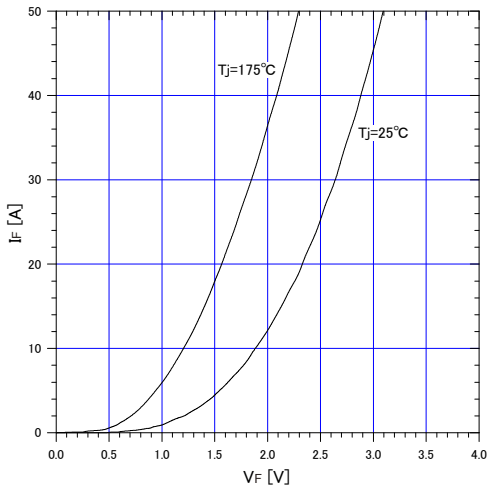
Graph.11  
Typical switching losses vs. Ic  
 $T_j=150^{\circ}C, V_{cc}=400V, L=500\mu H$   
 $V_{GE}=15V, R_G=10\Omega$



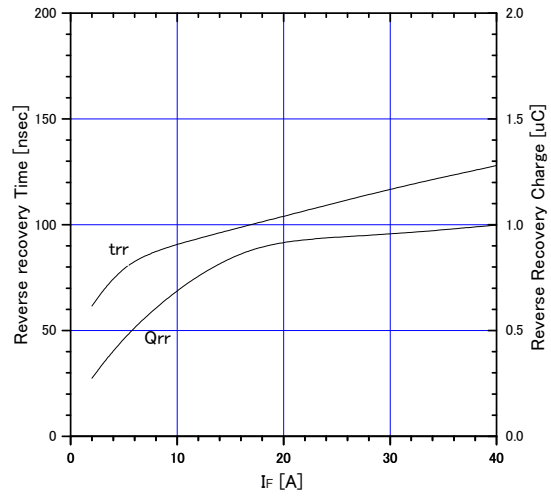
Graph.12  
Typical switching losses vs. Rg  
 $T_j=150^{\circ}C, V_{cc}=400V, I_c=20A, L=500\mu H$   
 $V_{GE}=15V$



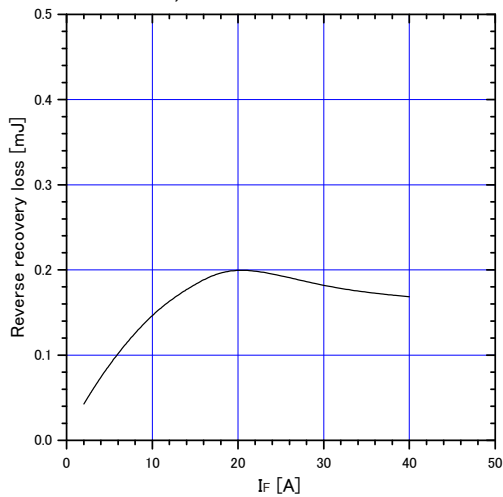
Graph.13  
FWD Forward voltage drop ( $V_F$ - $I_F$ )



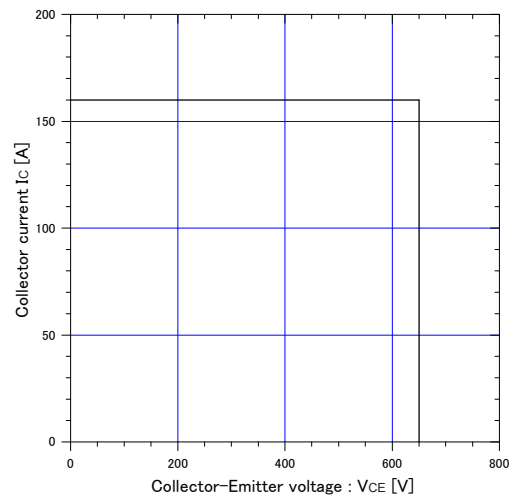
Graph.14  
Typical reverse recovery characteristics vs.  $I_F$   
 $T_J = 15^\circ\text{C}$ ,  $V_{CC} = 400\text{V}$ ,  $L = 500\mu\text{H}$   
 $V_{GE} = 15\text{V}$ ,  $R_G = 10\Omega$



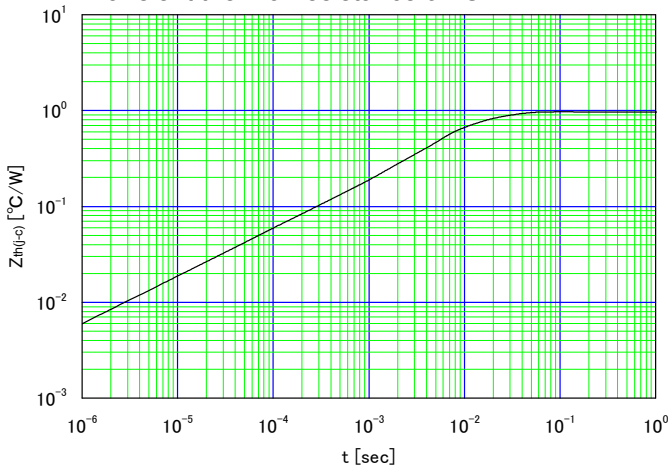
Graph.15  
Typical reverse recovery loss vs.  $I_F$   
 $T_J = 150^\circ\text{C}$ ,  $V_{CC} = 400\text{V}$ ,  $L = 500\mu\text{H}$   
 $V_{GE} = 15\text{V}$ ,  $R_G = 10\Omega$



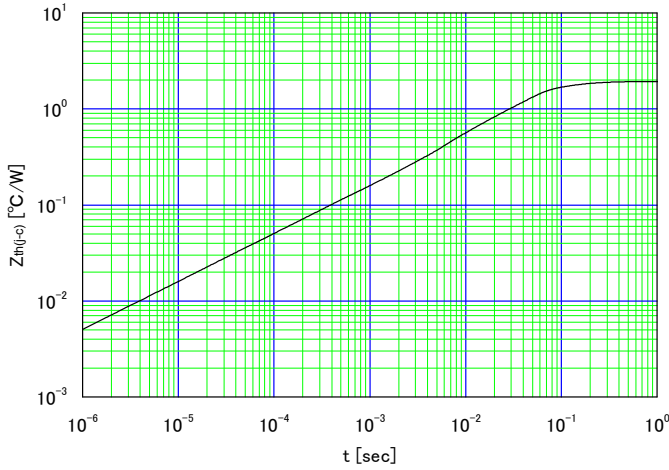
Graph.16  
Reverse biased Safe Operating Area  
 $T_J \leq 175^\circ\text{C}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 10\Omega$



Graph.17  
Transient thermal resistance of IGBT

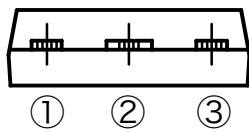
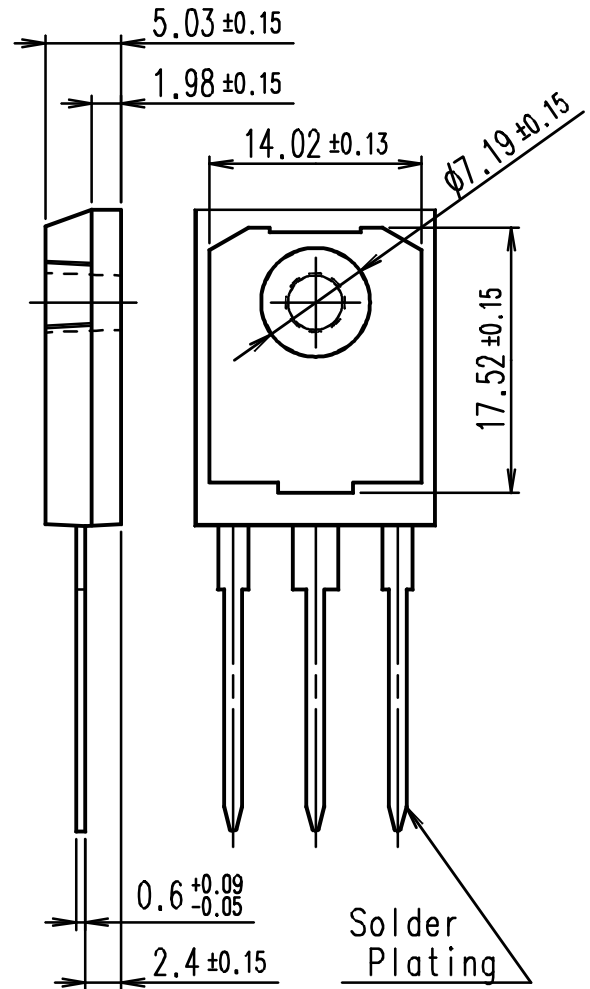
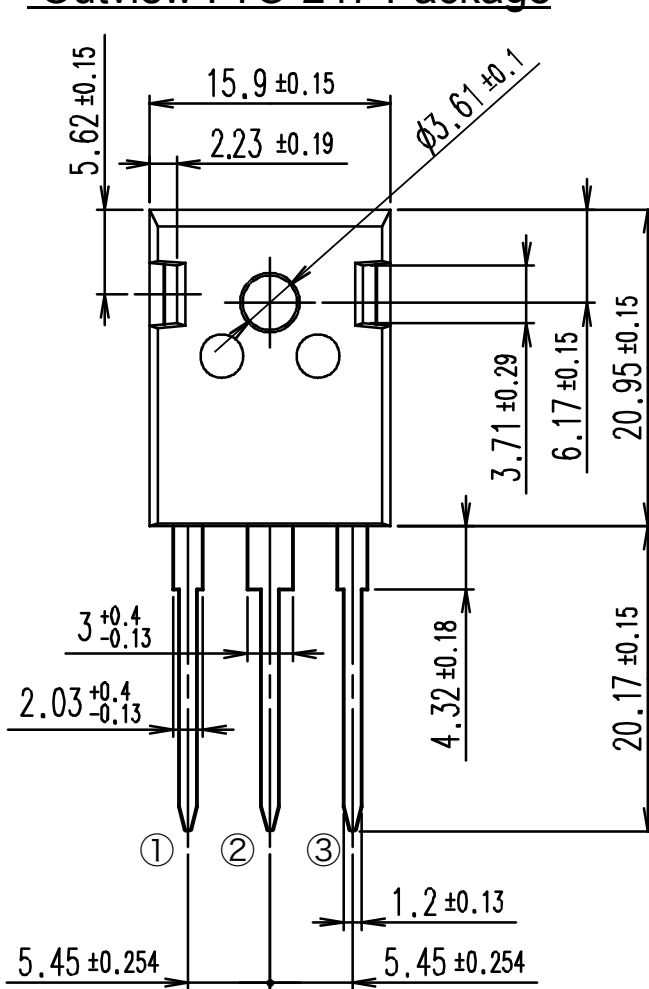


Graph.18  
Transient thermal resistance of FWD



■ Outline Drawings, mm

Outview : TO-247 Package



- CONNECTION
- ① GATE
  - ② COLLECTOR
  - ③ EMITTER

DIMENSIONS ARE IN MILLIMETERS.

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  - Measurement equipment
  - Machine tools
  - Audiovisual equipment
  - Electrical home appliances
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  - Safety devices
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